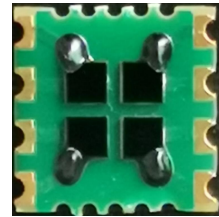


Technical Data Sheet

Four Quadrant Si PIN Photodiode: PDA5928

■ Features

- . 4 photodiodes
- . Quadrant element format
- . Fast response time
- . High photo sensitivity
- . Pb free
- . The product itself will remain within RoHS compliant version.



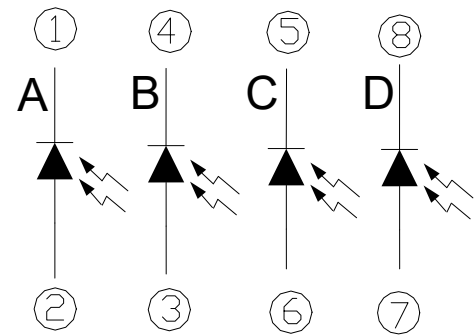
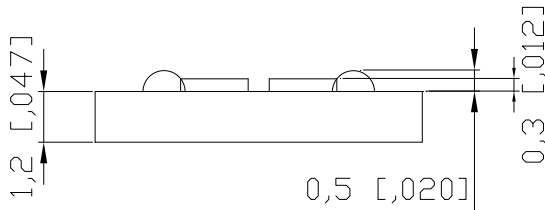
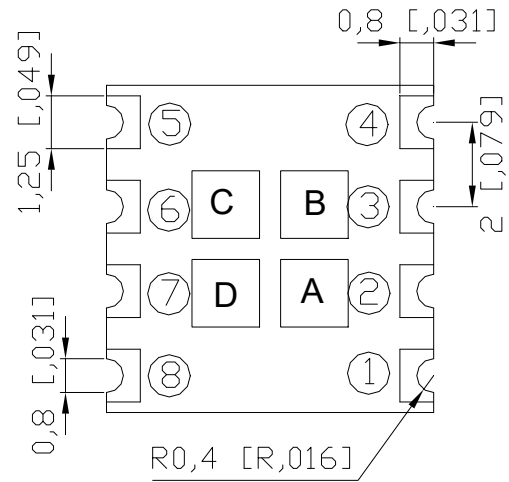
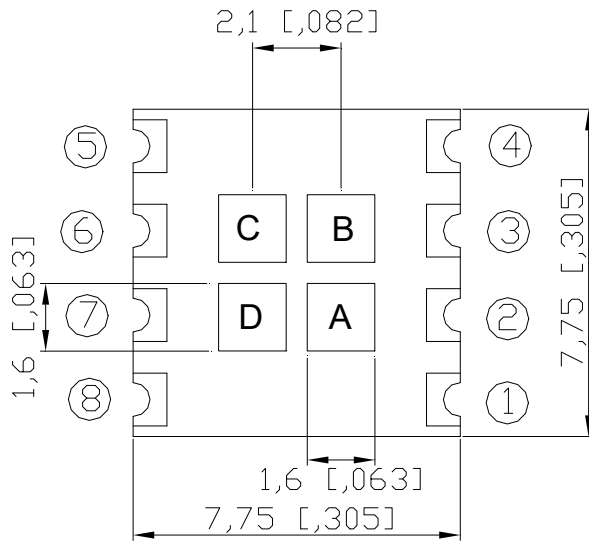
■ Descriptions

PDA5928 is an array of 4 high sensitive and high speed silicon photodiodes mounted on PCB.

■ Applications

- . Position sensing
- . Displacement monitoring
- . Track and Explore
- . Laser beam axis alignment

Package Dimensions



② ③ ⑥ ⑦ Anode

① ④ ⑤ ⑧ Cathode

- Note: 1. All dimensions are in millimeters(inches)
 2. Tolerances unless dimensions $\pm 0.25\text{mm}$ (.01")

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Units
Reverse Voltage	VR	30	V
Power Dissipation	Pd	150	mW
Lead Soldering Temperature	Tsol	260	$^\circ\text{C}$
Operating Temperature	Topr	-20 ~ +85	$^\circ\text{C}$
Storage Temperature	Tstg	-40 ~ +85	$^\circ\text{C}$

■ Electro-Optical Characteristics (Ta=25°C) (For per element)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Range of Spectral Bandwidth	$\lambda_{0.5}$	----	430	----	1100	nm
Wavelength of Peak Sensitivity	λ_p	----	----	940	----	nm
Open-Circuit Voltage	V _{OC}	Note(1)	----	0.32	----	V
Short- Circuit Current	I _{SC}	Note(1)	----	20	----	μ A
Reverse Light Current	I _L	Note(1) V _R =5V	----	20	----	μ A
Dark Current	I _d	Ee=0m W/cm ² V _R =10V	----	----	10	nA
Reverse Breakdown Voltage	BV _R	Ee=0m W/cm ² I _R =100 μ A	30	----	----	V
Total Capacitance	C _t	Ee=0m W/cm ² V _R =3V f=1MHZ	----	15	----	pF
Rise/Fall Time	t _r /t _f	V _R =10V R _L =1K Ω		30/30		nS

Note(1): Parallel light of 1000 Lux illumination is applied by a Tungsten lamp of 2856K

■ Typical Electro-Optical Characteristics Curves

Fig.1 Power Dissipation vs. Ambient Temperature

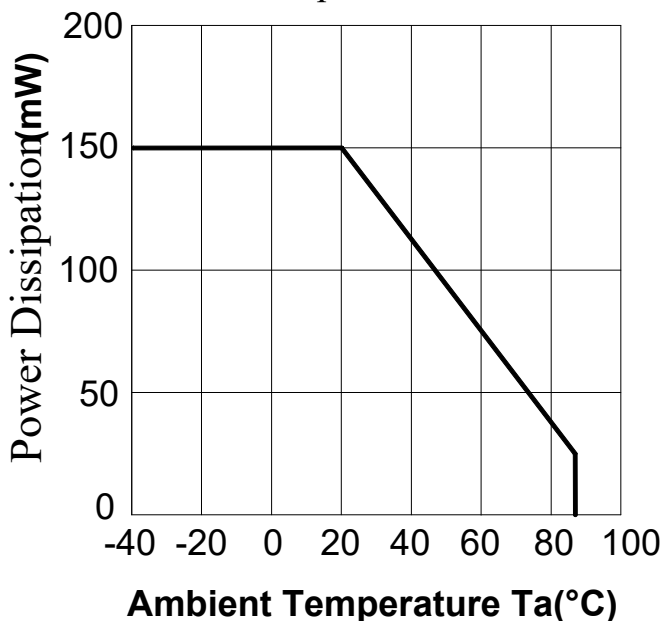


Fig.2 Spectral Sensitivity

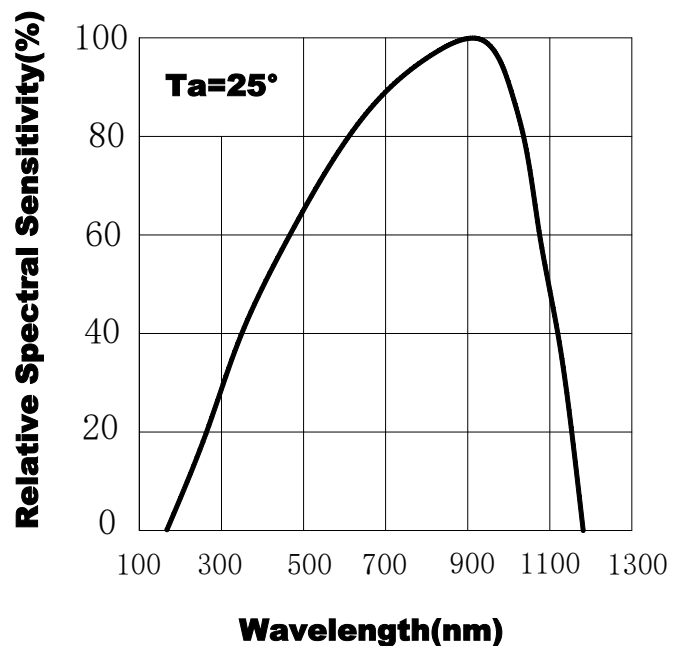


Fig.3 Dark Current vs. Ambient Temperature

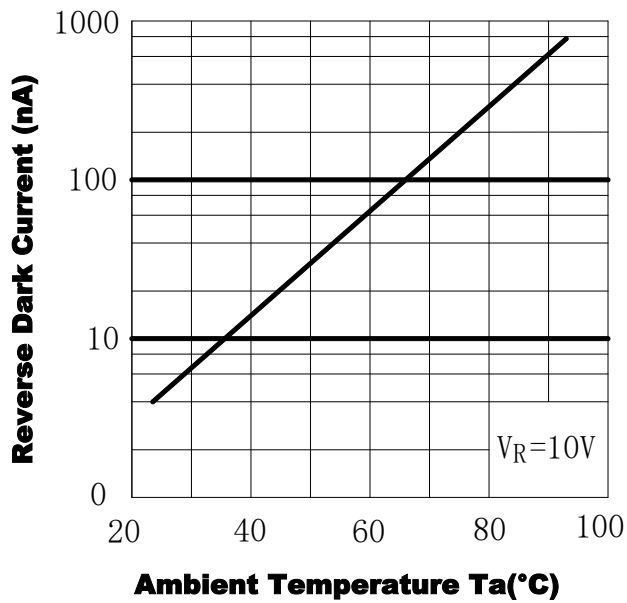
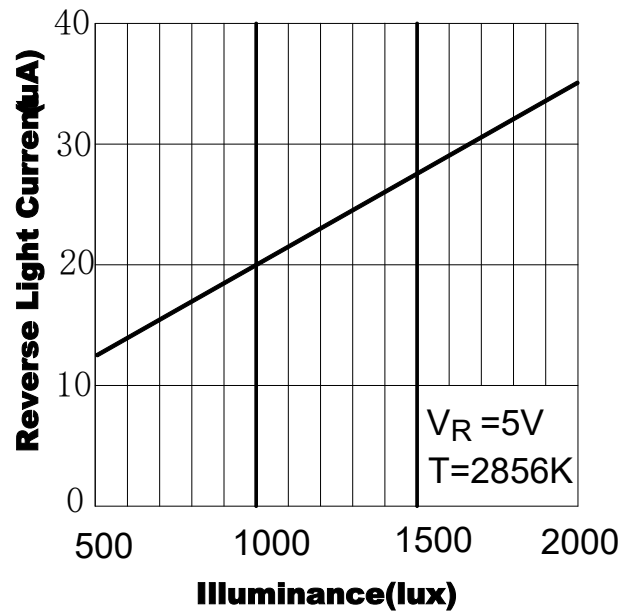

 Fig.4 Reverse Light Current vs. E_e


Fig.5 Terminal Capacitance vs. Reverse Voltage

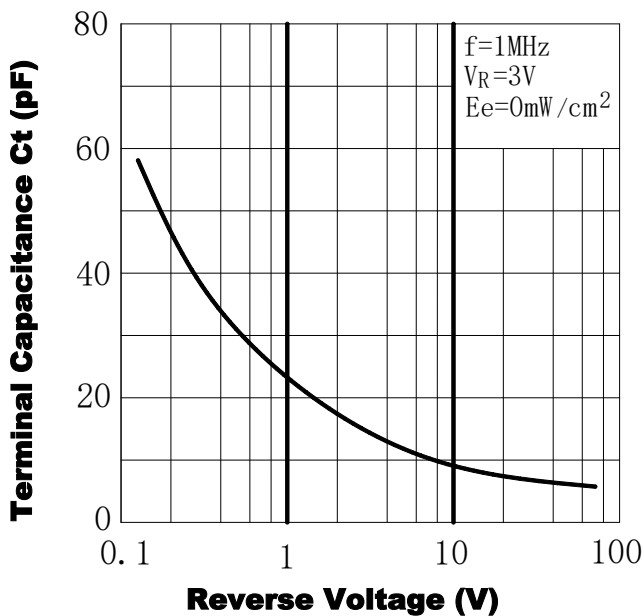
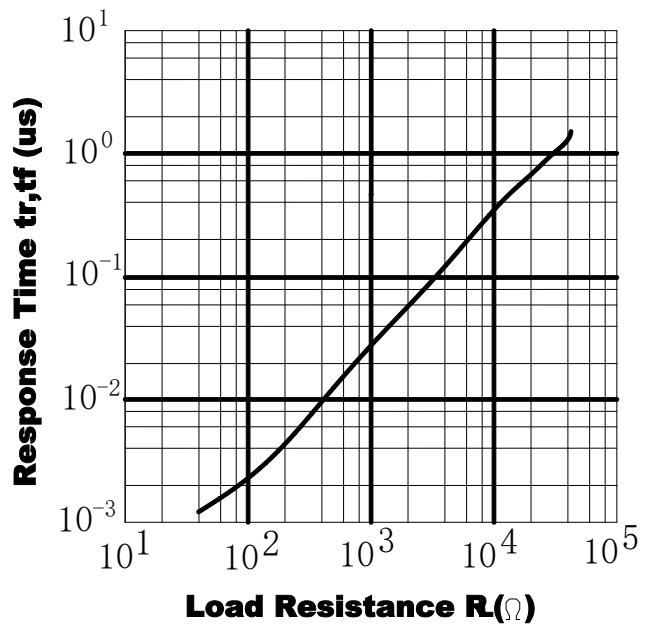


Fig.6 Response Time vs. Load Resistance



■ Notes

1. Above specification may be changed without notice. SHUGUAN will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. SHUGUAN assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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4. This products is bare chip products (wafers or diced chips), Unsealed products are not protected by an external enclosure and so require especially strict care to prevent physical breakage or contamination. It has protective tape, which is removed prior to use.
5. Condensation may form on the chip surface in environments subject to sharp or sudden fluctuations in temperature, so avoid use in such locations.
6. Applying excessive force to the product using a printed circuit board may cause the board to warp. This warping may damage the chip,wires connections, so use caution.
7. Do not let anything come in contact with the chip surface. Though the chip is hard, it is also brittle an easily notched. Sharped or hard items that come in contact with the chip may case cracks or scratches, which can lead to fluctuations in electrical characteristics or poor device reliability. Treat any products that were dropped as defect parts and dispose of them.